

planes detected by Electron backscatter diffraction; and

the semiconductor film contains less than 5×10^{18} nitrogen atoms per cm^3 , less than 5×10^{18} carbon atoms per cm^3 , and less than 1×10^{19} oxygen atoms per cm^3 .

[Claim 3]

5 A semiconductor film having a crystal structure with the composition ratio of germanium to silicon being 0.1 atomic percent or more and 10 atomic percent or below, characterized in that

the {101} plane in the semiconductor film reaches 30% or more of all the lattice planes detected by Electron backscatter diffraction; and

10 being obtained by crystallizing an amorphous semiconductor film formed by intermittent electric discharge while setting the repetition frequency to 10 kHz or below and the duty ratio to 50% or below.

[Claim 4]

A semiconductor film having a crystal structure with the composition ratio of 15 germanium to silicon being 0.1 atomic percent or more and 10 atomic percent or below, characterized in that

the {101} plane in the semiconductor film reaches 30% or more of all the lattice planes detected by Electron backscatter diffraction;

containing less than 5×10^{18} nitrogen atoms per cm^3 , less than 5×10^{18} carbon 20 atoms per cm^3 , and less than 1×10^{19} oxygen atoms per cm^3 ; and

being obtained by crystallizing an amorphous semiconductor film formed by intermittent electric discharge while setting the repetition frequency to 10 kHz or below and the duty ratio to 50% or below.

[Claim 5]

25 A semiconductor film according to any one of claims 1 to 4, wherein the

thickness of the semiconductor film is 10 nm through 100 nm.

[Claim 6]

A semiconductor device, wherein:

a channel formation region is formed from a semiconductor film and the
5 semiconductor film has a crystal structure with a composition ratio of germanium to silicon
being 0.1 atomic percent to 10 atomic percent or below; and

the {101} plane in the semiconductor film having a crystal structure reaches
30% or more of all the lattice planes detected by Electron backscatter diffraction.

[Claim 7]

10 A semiconductor device, wherein:

a channel formation region is formed from a semiconductor film and the
semiconductor film has a crystal structure with the composition ratio of germanium to
silicon being 0.1 atomic percent or more and 10 atomic percent or below; and

the {101} plane in the semiconductor film reaches 30% or more of all the lattice
15 planes detected by Electron backscatter diffraction; and the semiconductor film contains less
than 5×10^{18} nitrogen atoms per cm^3 , less than 5×10^{18} carbon atoms per cm^3 , and less than
 1×10^{19} oxygen atoms per cm^3 .

[Claim 8]

A semiconductor device, wherein:

20 a channel formation region is formed from a semiconductor film and the
semiconductor film has a crystal structure with the composition ratio of germanium to
silicon being 0.1 atomic percent or more and 10 atomic percent or below;

the {101} plane in the semiconductor film reaches 30% or more of all the lattice
planes detected by Electron backscatter diffraction; and

25 the semiconductor film is obtained by crystallizing an amorphous semiconductor

film formed by intermittent electric discharge while setting the repetition frequency to 10 kHz or below and the duty ratio to 50% or below.

[Claim 9]

A semiconductor device, wherein:

5 a channel formation region is formed from a semiconductor film and the semiconductor film has a crystal structure with the composition ratio of germanium to silicon being 0.1 atomic percent or more and 10 atomic percent or below;

the {101} plane in the semiconductor film reaches 30% or more of all the lattice planes detected by Electron backscatter diffraction;

10 the semiconductor film contains less than 5×10^{18} nitrogen atoms per cm^3 , less than 5×10^{18} carbon atoms per cm^3 , and less than 1×10^{19} oxygen atoms per cm^3 ; and

the semiconductor film is obtained by crystallizing an amorphous semiconductor film formed by intermittent electric discharge while setting the repetition frequency to 10 kHz or below and the duty ratio to 50% or below.

15 [Claim 10]

A semiconductor device according to any one of claims 6 to 9, wherein the thickness of the semiconductor film is 10 nm through 100 nm.

[Claim 11]

A method of manufacturing a semiconductor device comprising of:

20 a first step of forming an amorphous semiconductor film by plasma CVD through intermittent electric discharge, the amorphous semiconductor film containing germanium with a composition ratio of 0.1 atomic percent or more and 10 atomic percent or below to silicon; and

25 a second step of doping the amorphous semiconductor film with an element for promoting crystallization of the amorphous semiconductor film, and then subjecting the film

to heat treatment to form a semiconductor film having a crystal structure,

wherein the {101} plane in the semiconductor film having a crystal structure reaches 30% or more of all the lattice planes detected by Electron backscatter diffraction.

[Claim 12]

5 A method of manufacturing a semiconductor device comprising:

a first step of forming an amorphous semiconductor film by plasma CVD through intermittent electric discharge, the amorphous semiconductor film containing germanium with a composition ratio of 0.1 atomic percent or more and 10 atomic percent or below to silicon, the amorphous semiconductor film containing less than 5×10^{18} nitrogen 10 atoms per cm^3 , less than 5×10^{18} carbon atoms per cm^3 , and less than 1×10^{19} oxygen atoms per cm^3 ; and

a second step of doping the amorphous semiconductor film with an element for promoting crystallization of the amorphous semiconductor film, and then subjecting the film to heat treatment to form a semiconductor film having a crystal structure,

15 wherein the {101} plane in the semiconductor film having the crystal structure reaches 30% or more of all the lattice planes detected by Electron backscatter diffraction.

[Claim 13]

A method of manufacturing a semiconductor device comprising f:

a first step of forming an amorphous semiconductor film by plasma CVD 20 through intermittent electric discharge while setting the repetition frequency to 10 kHz or below and the duty ratio to 50% or less, the amorphous semiconductor film containing germanium with a composition ratio of 0.1 atomic percent or more and 10 atomic percent or below to silicon; and

a second step of doping the amorphous semiconductor film with an element for 25 promoting crystallization of the amorphous semiconductor film, and then subjecting the film

to heat treatment to form a semiconductor film having a polycrystal structure,
wherein the {101} plane in the semiconductor film having a crystal structure
reaches 30% or more of all the lattice planes detected by Electron backscatter diffraction.

[Claim 14]

5 A method of manufacturing a semiconductor device comprising:
a first step of forming an amorphous semiconductor film by plasma CVD
through intermittent electric discharge while setting the repetition frequency to 10 kHz or
below and the duty ratio to 50% or less, the amorphous semiconductor film containing
germanium with a composition ratio of 0.1 atomic percent or more and 10 atomic percent or
10 less to silicon, the amorphous semiconductor film containing less than 5×10^{18} nitrogen
atoms per cm^3 , less than 5×10^{18} carbon atoms per cm^3 , and less than 1×10^{19} oxygen atoms
per cm^3 ; and

a second step of doping the amorphous semiconductor film with an element for
promoting crystallization of the amorphous semiconductor film, and then subjecting the film
15 to heat treatment to form a semiconductor film having a crystal structure,

wherein the {101} plane in the semiconductor film having a polycrystal
structure reaches 30% or more of all the lattice planes detected by Electron backscatter
diffraction.

[Claim 15]

20 A method of manufacturing a semiconductor device according to any one of
claims 11 to 14, wherein the thickness of the amorphous semiconductor film is 10 nm
through 100 nm.

[Claim 16]

A method of manufacturing a semiconductor device comprising:
25 a first step of forming an amorphous semiconductor film by plasma CVD

through intermittent electric discharge, the amorphous semiconductor film containing germanium with a composition ratio of 0.1 atomic percent or more and 10 atomic percent or below to silicon; and

5 a second step of doping the amorphous semiconductor film with an element for promoting crystallization of the amorphous semiconductor film, and then subjecting the film to heat treatment to form a semiconductor film having a crystal structure,

wherein a channel formation region is formed from the semiconductor film having the crystal structure, and

10 wherein the {101} plane in the semiconductor film having the crystal structure reaches 30% or more of all the lattice planes detected by Electron backscatter diffraction.

[Claim 17]

A method of manufacturing a semiconductor device comprising f:

a first step of forming an amorphous semiconductor film by plasma CVD through intermittent electric discharge, the amorphous semiconductor film containing 15 germanium with a composition ratio of 0.1 atomic percent or more and 10 atomic percent or below to silicon, the amorphous semiconductor film containing less than 5×10^{18} nitrogen atoms per cm^3 , less than 5×10^{18} carbon atoms per cm^3 , and less than 1×10^{19} oxygen atoms per cm^3 ; and

20 a second step of doping the amorphous semiconductor film with an element for promoting crystallization of the amorphous semiconductor film, and then subjecting the film to heat treatment to form a semiconductor film having a crystal structure,

wherein a channel formation region is formed from the semiconductor film having the crystal structure, and

25 wherein the {101} plane in the semiconductor film having the crystal structure reaches 30% or more of all the lattice planes detected by Electron backscatter diffraction.

15 [Claim 18]

A method of manufacturing a semiconductor device comprising:

a first step of forming an amorphous semiconductor film by plasma CVD through intermittent electric discharge while setting the repetition frequency to 10 kHz or 5 below and the duty ratio to 50% or less, the amorphous semiconductor film containing germanium with a composition ratio of 0.1 atomic percent or more and 10 atomic percent or below to silicon; and

10 a second step of doping the amorphous semiconductor film with an element for promoting crystallization of the amorphous semiconductor film, and then subjecting the film to heat treatment to form a semiconductor film having a crystal structure,

wherein a channel formation region is formed from the semiconductor film having the crystal structure, and

wherein the {101} plane in the semiconductor film having the crystal structure reaches 30% or more of all the lattice planes detected by Electron backscatter diffraction.

15 [Claim 19]

A method of manufacturing a semiconductor device comprising:

a first step of forming an amorphous semiconductor film by plasma CVD through intermittent electric discharge while setting the repetition frequency to 10 kHz or 20 below and the duty ratio to 50% or less, the amorphous semiconductor film containing germanium with a composition ratio of 0.1 atomic percent or more and 10 atomic percent or less to silicon, the amorphous semiconductor film containing less than 5×10^{18} nitrogen atoms per cm^3 , less than 5×10^{18} carbon atoms per cm^3 , and less than 1×10^{19} oxygen atoms per cm^3 ; and

25 a second step of doping the amorphous semiconductor film with an element for promoting crystallization of the amorphous semiconductor film, and then subjecting the film